

Construction of RIO codes for improved SSD random read

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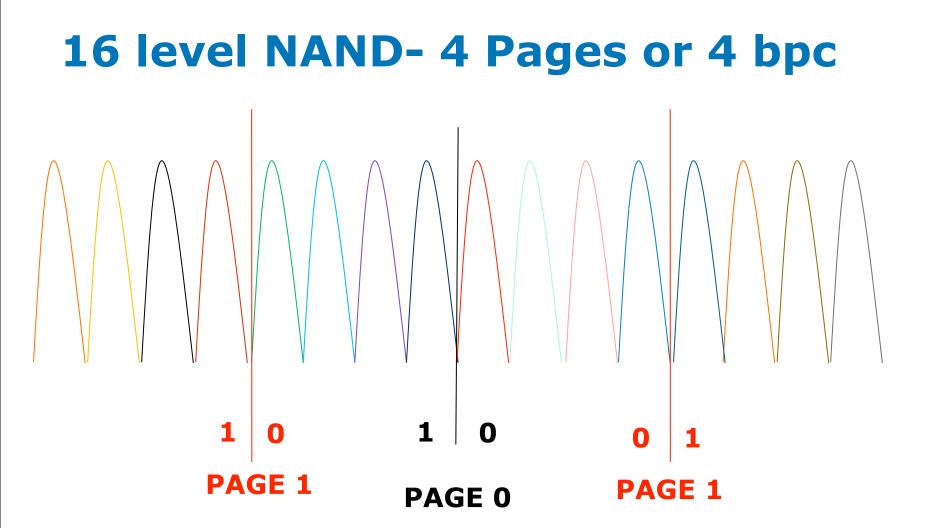
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Random I/O Codes (RIO Codes)

- Introduced by Eran and Idan at NVM Workshop 2013
- Established a correspondence between WOM codes and RIO codes
- A WOM code which allows writing k bits into n cells t times
- RIO code which allows programming k bits into n cells for t pages such that each page can be read with a single strobe operation for the t + 1 level NAND

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Need 1 sensing from NAND for Page 0, 2 senses for Page 1 4 senses for Page 2, 8 senses for Page 3

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RIO Codes

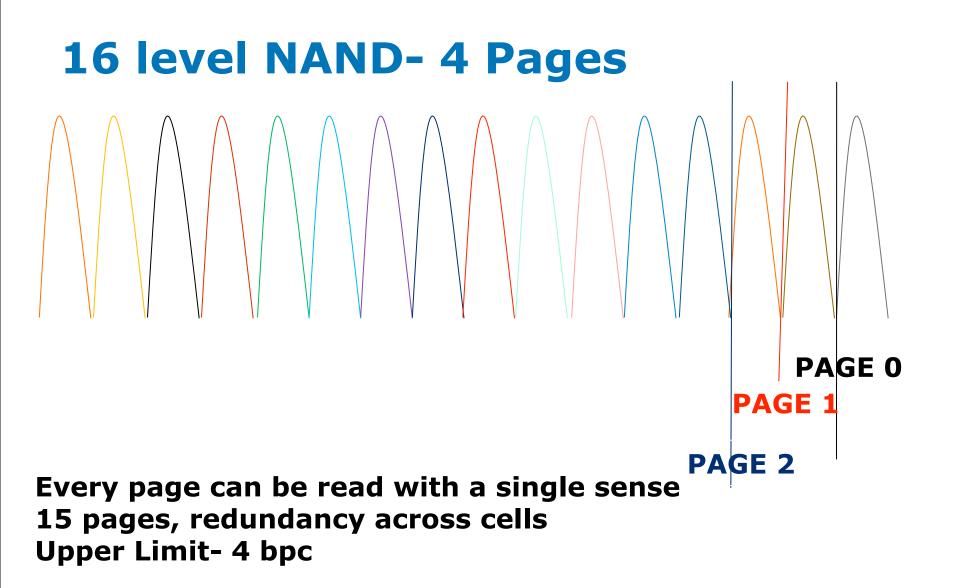
- Strobes for 4 bpc
 - Page 0- 1 strobe
 - Page 1- 2 strobes
 - Page 2- 4 strobes
 - Page 3- 8 strobes
- For 4 bits per cell NAND, average reads to read one page is 3.75
- Read latency increases as levels increase
- To improve performance for MLC NAND, use Random I/O Codes

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WOM code

- Allows writing k bits to n cells t times without erasing (overwriting t 1 times)
- Example (n, k, t) = (3, 2, 2) WOM code (1.33 bpc)

2 bits to write	1 st write in SLC NAND	2 nd write in SLC NAND
00	000	111
01	001	110
10	010	101
11	100	011

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Three-level NAND RIO Code

- Page 2 Page 1
- Read page 1 by putting a strobe between level 1 and level 2
- Read page 2 by putting a strobe between level 0 and level 1

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Scope of this work

- For a given n, k, t, does there exist an RIO code?
- If there exists a WOM code for given (n, k, t), then there exists an RIO code
- No existence proof for WOM codes
- There is a bound on the rate for RIO codes derived by Eran et. al.
- Even if the considered rate is lower than the bound there may not exist an RIO code
- An algorithm to check if there exists an RIO code for a given (n, k, t)

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RIO Code (*n*, *k*, *t*)

- n = 4, 2k = 6, t = 2
- k = 3, 3 bits per page
- $2^6 = 64$ combinations to be programmed
- 4 cells can be programmed to $3^4 = 81$ possible states
- 81 64 = 17 programming states have to be eliminated
- Two pages to be programmed
 - Page 1 read by putting a strobe between level 1 and level 2
 - Page 2 read by strobe between level 0 and level 1
- 8 combinations for each page (3 bits per page)
- Arrange the 8 combinations for each page as rows and columns of a 2-D matrix



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Table with entries for the two

pages

Bits from Page 2/ Page 1 read	1111 уууу у - {0,1} A ₁₅	1110 yyyy2 A ₁₄	1101 <i>yy2y</i> <i>A</i> ₁₃	1011 y2yy _{A11}	0111 2yyy A ₇	уу22	y2y2	y22y
0000 xxxx $x - \{1,2\}$ B_{15}	1111	1112	1121	1211	2111	?	?	?
0001 xxx0 B ₁₄	1110	х	1120	1210	2110	?	?	?
0010 xx0x B ₁₃	1101	1102	х	1201	2101	?	?	?
0100 x0xx B ₁₁	1011	1012	1021	Х	2011	?	?	?
1000 0 <i>xxx</i> <i>B</i> ₇	0111	0112	0121	0211	х	?	?	?
x00x	?	0002	?	?	?	?	?	?
00xx	?	0012	?	?	?	?	?	?
0x0x	?	0102	?	?	?	?	?	?

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RIO Code (*n*, *k*, *t*)

- 4 cells imply that there are 16 possibilities for bits read
- Combine 16 possibilities read for each page into 8 groups
- Each group is either a column (for Page 1) or a row (for Page 2)
- Any one possible read combination can occupy atmost one row or column



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Enumerate Program states for Page 1

- Strobe between level 1 and level 2
- Read bits and programmed levels
- · At most 8 programmed levels from each row can be used
- · From the yyyy programmed levels, 8 entries cannot be used

Bits read from NAND	Programmed levels	Total number	Name of the set which stores the programmed levels					
0000	2222	1	A ₀					
0001	222y $y - \{0,1\}$	2	A_1					
0010	22y2	2	A_2					
0011	22уу	4	A_3					
0100	2y22	2	A_4					
0101	2 <i>y</i> 2 <i>y</i>	4	A_5					
0110	2уу2	4	A_6					
0111	2ууу	8	A ₇					
1000	y222	2	A_8					
1001	y22y	4	A ₉					
1010	y2y2	4	A ₁₀					
1011	у2уу	8	A ₁₁					
1100	уу22	4	A ₁₂					
1101	уу2у	8	A ₁₃					
1110	ууу2	8	A14					
1111	уууу	16	A ₁₅					
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Page 2

- Strobe between level 0 and level 1
- · At most 8 programmed levels from each row can be used
- From the xxxx programmed levels, 8 entries cannot be used

Bits read from NAND	Programmed levels	Total number	Name of the set which stores the programmed levels
0000	$xxxx x - \{1,2\}$	16	B ₁₅
0001	0xxx	8	B_{14}
0010	xx0x	8	B ₁₃
0011	<i>xx</i> 00	4	B ₁₂
0100	x0xx	8	B ₁₁
0101	<i>x</i> 0 <i>x</i> 0	4	B ₁₀
0110	x00x	4	B_9
0111	x000x	2	B ₈
1000	0xxx	8	B7
1001	0xx0	4	B_6
1010	0x0x	4	B ₅
1011	0x00	2	B_4
1100	00xx	4	B_3
1101	0x00	2	B2
1110	000 <i>x</i>	2	B_1
1111	0000	1	B ₀
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How many programming levels cannot be used

- Allowed to drop $3^4 2^6 = 17$ possibilities
- 8 programming states corresponding to set A_{15} cannot be used
- 8 programming states corresponding to set B_{15} cannot be used
- 16 programing states are out

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How many programming states are not allowed?

Bits from Page 2/ Page 1 read	$ 1111 yyyy y - {0,1} A_{15} $	1110 <i>yyy2</i> <i>A</i> 14	1101 <i>yy2y</i> <i>A</i> ₁₃	1011 y2yy A ₁₁	0111 2 <i>yyy</i> <i>A</i> 7
0000 xxxx $x - \{1,2\}$ B_{15}	1111	1112	1121	1211	2111
0001 xxx0 B ₁₄	1110	x	1120	1210	2110
0010 xx0x B ₁₃	1101	1102	x	1201	2101
0100 <i>x0xx</i> <i>B</i> ₁₁	1011	1012	1021	x	2011
1000 0 <i>xxx</i> <i>B</i> ₇	0111	0112	0121	0211	x

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How many programming states are out?

- In addition to the 16 already ousted, there are at least 4 more states which are not allowed
- 20 programming levels are forbidden by the RIO code
- Conclusion- There does not exist an RIO code for (4,3,2) case



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Algorithm to check existence

• Generate intuition from (4,3,2) case to generalize to any (n, k, t)



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Existence for (*n*, *k*, 2)

- Define sets A and B for Page 1 and Page 2 resp.
- A^J_i defined for Page 1 such that it includes all the possible programmed n-cells such that
 - -i out of n cells are programmed to level 0 or 1
 - J is the set of indices which are programmed to level 0 or 1
- Example
 - $-n = 10, i = 6, J = \{1, 2, 3, 7, 8, 10\}$
 - $-A_6^J = \{0002220020, 0002220021, 0002220120, \dots, 1112221121\}$
- A_i^J has 2^i elements and for each *i*, total number of J sets are nC_i
- For Page 2, define sets B^J_i where i out of n cells are programmed to level 1 or 2

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Existence for (*n*, *k*, 2)

- Sets A_i^J and B_i^J , i = 0, 1, ..., n
- A_n^J and B_n^J each have 2^n elements each
- Upto 2^k elements can be chosen from each of these sets
- $2(2^n 2^k)$ programmed states are out
- Sets A_{n-1}^{J} and B_{n-1}^{J} each have 2^{n-1} elements
- Upto 2^k elements can be chosen from each set
- 2n(2ⁿ⁻¹-2^k)programmed states are out



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Existence for (*n*, *k*, 2)

- For set A_i^J , out of the 2^{n-i} programmed states, 2^k can only be taken
- Total programmed states dropped out for all A_i^J and B_i^J are 2. ${}^{n}C_i$. $(2^{n-i} - 2^k)$
- Sum the drop-outs over all *i* to get

$$\sum_{i=0}^{n} 2 \cdot C_{i} \cdot (2^{n-i} - 2^{k}), i \ge n - i > k$$

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Drop-outs due to intersection of sets *A* and *B*

- Intersection of programming states from sets A_i^J and B_l^Y
- If sets J^c and Y^c intersect, the elements in the intersection cannot be programmed
- Those are the drop-outs
- A_n^J and B_n^Y lead to no drop-outs since $J^c \cap Y^c = \emptyset$
- A_{n-1}^J and B_{n-1}^Y have one drop-out as Y runs across the n combinations for a fixed J
- *n* dropouts follow from the intersection of A_{n-1}^{J} and B_{n-1}^{Y} as we span all sets *J* and *Y*

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Drop-outs due to intersection of states from *A* and *B*

- A_{n-1}^J and B_{n-2}^Y have at least one drop-out as Y runs across the n combinations for a fixed J
- Given the locations programmed to level 2 in set J^c , the probability that location intersects with a location in Y^c for Y in B_{n-2}^Y equals $\frac{2}{n}$
- Total possibilities for Y in B_{n-2}^{Y} is ${}^{n}C_{2}$
- Total drop-outs = ${}^{n}C_{2} \frac{2}{n}$
- Total drop-outs over all $J = n {}^{n}C_{2} \frac{2}{n}$





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Drop-outs due to intersection of states from A and B

- Intersection of states in A_i^J and B_l^Y , $i \leq l$
- Consider A_i^J , what is the probability that the *l* coordinates in Y^c match with any one of the *i* coordinates in J^c ?
- Probability that match at none of the *i* locations =

$$\mathsf{P} = \frac{n-l}{n} \cdot \frac{n-l-1}{n-1} \cdot \frac{n-l-2}{n-2} \dots \cdot \frac{n-(l-i+1)}{n-(i-1)}$$

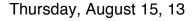
• Given the locations programmed to level 2 in set J^c , the probability that location intersects with any of the location in Y^c of B_l^Y equals 1 - P

• Total drop-outs =
$${}^{n}C_{l}{}^{n}C_{i}$$
 (1 – P)

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Construction by filling table

	A_n^J	$A_{n-1}^{J_1}$	$A_{n-1}^{J_2}$	$A_{n-1}^{J_3}$	 $A_{n-1}^{J_n}$	$A_{n-2}^{J_{n+1}}$	$A_{n-2}^{J_{n+2}}$	
	$J^c \cap Y^c = \emptyset$							
$B_{n-1}^{Y_1} \\ B_{n-1}^{Y_2} \\ B_{n-1}^{Y_3} \\ B_{n-1}^{Y_3}$								
$B_{n-1}^{Y_2}$								
$B_{n-1}^{Y_3}$								
$B_{n-1}^{Y_n}$								
$B_{n-2}^{Y_{n+1}}$								
$B_{n-1}^{Y_n}$ $B_{n-2}^{Y_{n+1}}$ $B_{n-2}^{Y_{n+2}}$								

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Generalized RIO Coding

- RIO code does not exist for (4,3,2)
- If requirement is 1.5 bpc
- Generalized RIO Code- Permits reading some pages with one read and others allowed to have 2 or multiple reads



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Generalized RIO code with 1.5 bpc for t=2 • 4 cells store 6 bits -> 1.5bpc

• 2 pages with 3 bits each

	Strobe L1 L2 L0 L1	1111	1110	1101	1011	0111	1100/ 1010	1001/ 0110 1000	010/10 100/ 0011
	UP/LP	000	001	010	011	100	101	110	111
1110/0001	000	0001	0002	1120	1210	2110	0122	1220	2210
1101/0010	001	0010	1102	0020	1201	2101	1202	2102	2201
1011/0100	010	0100	1012	1021	0200	2011	1022	2012	2021
1001/0110	011	0110	1002	0120	0210	2001	1122	2002	2121
0111/1000	100	1000	0112	0121	0211	2000	0212	0221	2122
0101/1010	101	1010	0102	1020	0201	2010	0202	1222	2020
0011/1100	110	1100	0012	0021	1200	2100	0022	1221	2200
0000/1111	111	0000	1112	1121	1211	2111	1212	2112	2211

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Generalized RIO code for (4,3,2)

- The mapping permits reading one page (LP or Page 1) with a single strobe
- Applying a strobe between level 1 and level 2 gives 4 bits from 4 cells which can be uniquely mapped to 3 bits
- The second page (UP or Page 2) needs 2 strobes for unique decoding
- Page 2 read needs more than one strobe if the bits read out are 0000



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Generalize for any t

- For t = 3, we get a cube and for t = 4 onwards, a hypercube
- Principal of checking for existence and construction remain the same



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Mappings for minimizing RBER

- Once the mapping of the sets is done, it remains to decide how to map data bits to the RIO code bits
- For the (4,3,2) code, we need to map the 3 user or data bits to the 4 bits read from the NAND
- Mapping done to minimize the RBER
- n-cell voltages are closer to each other implies that the corresponding data bits are also close in Hamming distance
- 0001 and 0002 are two programmed states which are closest, so the assigned data bits are 000 and 001 resp.
- Reduces the BER amplification

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Impact of RIO coding on tI/O

- The transfer time increases due to redundancy of the RIO code
- (4,3,2) RIO code
- Instead of 3 bits output from the NAND (conventional), 4 bits are output (RIO code)
- Overhead of 33% as far as tI/O is concerned
- Solution- Perform RIO demapping within the NAND



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Generating soft information on input bits

- 3 data bits mapped to 4 RIO code bits
- $[u_0 \ u_1 \ u_2] \dashrightarrow [c_0 \ c_1 \ c_2 \ c_3]$
- Read from NAND $[r_0 r_1 r_2 r_3]$

•
$$LLR(u_0) = \ln \frac{P(u_0=0|[r_0 \ r_1 \ r_2 \ r_3])}{P(u_0=1|[r_0 \ r_1 \ r_2 \ r_3])}$$

$$= \ln \frac{P([r_0 \ r_1 \ r_2 \ r_3]|u_0=0)}{P([r_0 \ r_1 \ r_2 \ r_3]|u_0=1)}$$

$$= \ln \frac{\sum_{[c_0 \ c_1 \ c_2 \ c_3] \ni u_0=0} P([r_0 \ r_1 \ r_2 \ r_3]|[c_0 \ c_1 \ c_2 \ c_3])}{\sum_{[c_0 \ c_1 \ c_2 \ c_3] \ni u_0=1} P([r_0 \ r_1 \ r_2 \ r_3]|[c_0 \ c_1 \ c_2 \ c_3])}$$

$$= \ln \frac{\sum_{[c_0 \ c_1 \ c_2 \ c_3] \ni u_0=0} P(r_0|c_0)P(r_1|c_1)P(r_2|c_2)P(r_3|c_3)}{\sum_{[c_0 \ c_1 \ c_2 \ c_3] \ni u_0=1} P(r_0|c_0)P(r_1|c_1)P(r_2|c_2)P(r_3|c_3)}$$

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Summary and Conclusions

- A method to find if an RIO code exists for given parameters (n, k, t)
- The method is also constructive, it yields an RIO code
- Generalized RIO Code
- Mapping of user/data bits to the NAND read bits
- Impact on tI/O
- Generation of soft information



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